



# **isc Silicon NPN Power Transistor**

#### **DESCRIPTION**

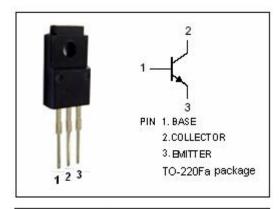
- · Low Collector Saturation Voltage
- : V<sub>CE(sat)</sub>= 0.5V(Max)@ I<sub>C</sub>= 2A
- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 80V (Min)
- · Good Linearity of hFE
- · High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

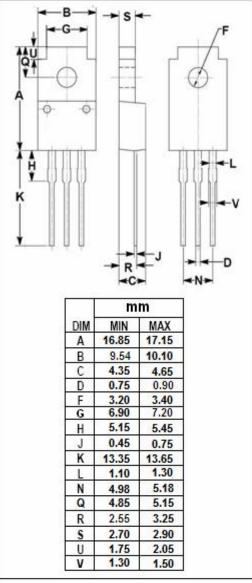
## **APPLICATIONS**



## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	130	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
lc	Collector Current-Continuous	2	А	
Ісм	Collector Current-Peak	5	Α	
P <sub>C</sub>	Collector Power Dissipation @ T <sub>C</sub> =25°C	25	w	
	Collector Power Dissipation @ T <sub>a</sub> =25℃	2		
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	







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2SD1517

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	80			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.1A			0.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.1A			1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0			10	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			50	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 2V	45			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 2V	60		260	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V; f= 10MHz		25		MHz
Switching times						
ton	Turn-on Time			0.1		μs
t <sub>stg</sub>	Storage Time	$I_{C}$ = 0.5A; $I_{B1}$ = - $I_{B2}$ = 50mA; $V_{CC}$ = 50V		2.5		μs
t <sub>f</sub>	Fall Time			0.3		μs

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•	n <sub>FF-2</sub>	classifications	:

R	Q	Р
60-120	90-180	130-260

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